

# UNITED STATES PATENT AND TRADEMARK OFFICE

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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/982,433	10/18/2001	Koichi Takeuchi	39792909-5224	6653	
33448	7590 04/16/	3			
ROBERT D	EPKE		EXAM	EXAMINER	
HOLLAND -	+ KNIGHT		KEBEDE	KEBEDE, BROOK	
CHICAGO, IL 60603			ART UNIT	PAPER NUMBER	
,			2823		
			DA.F.E MAILED: 04/16/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

PTO-90C (Rev. 07-01)

7-7-		Application No.	Applicant(s)	100
	<del>-</del>		TAKEUCHI, KOICHI	
Office Action Summans		09/982,433		
	Office Action Summary	Examiner	Art Unit	
		Brook Kebede	2823	
Period fo	The MAILING DATE of this communication ap or Reply	pears on the cover sheet	, was the consequence	
A SH THE I - Exten after - If the - Failu - Any	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a rep or period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statut reply received by the Office later than three months after the mailing patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may  ly within the statutory minimum of  will apply and will expire SIX (6) No  expression of the complexity of the complexity of the application to become	y a reply be timely filed thirty (30) days will be considered timely. MONTHS from the mailing date of this committee ABANDONED (35 U.S.C. § 133).	unication.
1)⊠	Responsive to communication(s) filed on 18	October 2001 .		
2a) <u></u>	7	his action is non-final.		
3)	Since this application is in condition for allow closed in accordance with the practice under	rance except for formal r	matters, prosecution as to the n C.D. 11, 453 O.G. 213.	nerits is
Disposit	ion of Claims	,		
4)⊠	Claim(s) 1-4 is/are pending in the application			
	4a) Of the above claim(s) is/are withdra	awn from consideration.		
5)	Claim(s) is/are allowed.			
•	Claim(s) <u>1-4</u> is/are rejected.			
	Claim(s) is/are objected to.			
	Claim(s) are subject to restriction and/	or election requirement.		
	ion Papers  The specification is objected to by the Examin	or		
, —	The specification is objected to by the Examina  The drawing(s) filed on is/are: a) accompany		ov the Examiner.	
10)	Applicant may not request that any objection to t			
11)	The proposed drawing correction filed on	_ is: a) ☐ approved b) [	disapproved by the Examiner.	
,	If approved, corrected drawings are required in re			
12)	The oath or declaration is objected to by the E	xaminer.		
Priority	under 35 U.S.C. §§ 119 and 120			
13)⊠	Acknowledgment is made of a claim for foreign	gn priority under 35 U.S.	C. § 119(a)-(d) or (f).	,
. a)	⊠ All b) Some * c) None of:			
	1. Certified copies of the priority documer	nts have been received.		
	2. Certified copies of the priority documer			
*	3. Copies of the certified copies of the pri application from the International B See the attached detailed Office action for a lis	Bureau (PCT Rule 17.2(a	a)).	age
	Acknowledgment is made of a claim for domes			oplication).
	a) The translation of the foreign language p Acknowledgment is made of a claim for dome	rovisional application ha	s been received.	
Attachme		· •		
1) 🔀 Noti 2) 🔲 Not	ice of References Cited (PTO-892) ice of Draftsperson's Patent Drawing Review (PTO-948) rmation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice	view Summary (PTO-413) Paper No(s). e of Informal Patent Application (PTO-1	52)

Application/Control Number: 09/982,433

Art Unit: 2823

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#### **DETAILED ACTION**

#### **Priority**

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

## Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1, 3 and 4 are rejected under 35 U.S.C. 102(b) as being anticipated by Ishibashi et al. (US/5,858,620).

Re claim 1, Ishibashi et al. disclose a pattern forming method, comprising the steps of: forming a first resist pattern (1) (see Fig. 2(b)) containing a photo-acid generating agent on a substrate (3); irradiating light to an exposed surface of the first resist pattern (see Col. 3, lines 23-39); coating a resist film (2) containing a cross-linking agent, which reacts with acid, on the substrate after irradiation of the light in a state where it covers the first resist pattern (1); causing a cross-linking reaction at an interface between the first resist pattern and the resist film to grow a cross-linked layer; and forming a second resist pattern (4) made of the cross-linked layer and the first resist pattern (see Figs. 2(a) – 4(g); Col. 1, line 33 – Col. 9, line 48).

Re claim 3, as applied to claim 1 above, Ishibashi et al. disclose all the claimed limitation including the limitation wherein a base resin of a resist material forming the first resist pattern

Application/Control Number: 09/982,433

Art Unit: 2823

containing the photo-acid generating agent is one selected from the group consisting of methacrylic resin and cycloolefin resin (see Col. 2, lines 5-9).

Re claim 4, as applied to claim 1 above, Ishibashi et al. disclose all the claimed limitation including the limitation wherein a base resin of the resist film containing the cross-linking agent, which reacts with the acid, is one selected from the group consisting of polyvinyl alcohol system resin, polyacrylic acid system resin, and polyvinyl acetal system resin (see Col. 2, lines 19-31; Col. 3, lines 53-67).

## Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claim 2 rejected under 35 U.S.C. 103(a) as being unpatentable over Ishibashi et al. (US/5,858,620) in view of

Re claim 2, as applied to claim 1 above, Ishibashi et al. disclose all the claimed limitations including the use of light. Although it is well-known in the art to use ArF excimer laser light and KrF excimer laser light during processing and patterning of resist film, Ishibashi et al. do not specifically disclose wherein the light is one selected from the group consisting of ArF excimer laser light and KrF excimer laser light.

Ohta et al. disclose the use of light selected from the group consisting of ArF excimer laser light and KrF excimer laser light during lithography process. Ohta et al. disclose that "Given as examples of such a short wavelength radiation are deep ultraviolet rays, such as a

Application/Control Number: 09/982,433

Art Unit: 2823

r,

bright line spectrum of a mercury lamp (wavelength 254 nm), a KrF excimer laser (wavelength 248 nm), and an ArF excimer laser (wavelength 193 nm); X-rays such as synchrotron radiation; and charged particle rays such as an electron beam. Of these, lithography using an excimer laser is attracting a great attention due to its high output and high efficiency. For this reason, the resists used in lithography also must produce minute patterns of 0.5 µm or less with high sensitivity and high resolution by excimer laser with good reproducibility." (see Col. 1, lines 28-39).

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to have provided Ishibashi et al. reference with KrF of ArF excimer laser light as taught by Ohta et al. because high output and high efficiency patterns would have been produced during lithography process.

#### Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure Iwasa et al. (US/5,770,346), Kumada et al. (US/5,981,146), Sato et al. (US/6,054,254), Endo et al. (US/6,074,804), Yamana (US/6,096,478), Yamaguchi (US/6,337,175), Schroeder et al. (US/6,379,869), and Iwasa et al. (US/6,437,052) also disclose similar inventive subject matter.

### Correspondent

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Brook Kebede whose telephone number is (703) 306-4511. The examiner can normally be reached on 8-5 Monday to Friday.

Page 5

Application/Control Number: 09/982,433

Art Unit: 2823

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Brook Kebede

April 10, 2003

W. DAVID COLEMAN PRIMARY EXAMINER